

Institute for Material Science, Chair "Material Science and Nanotechnology"

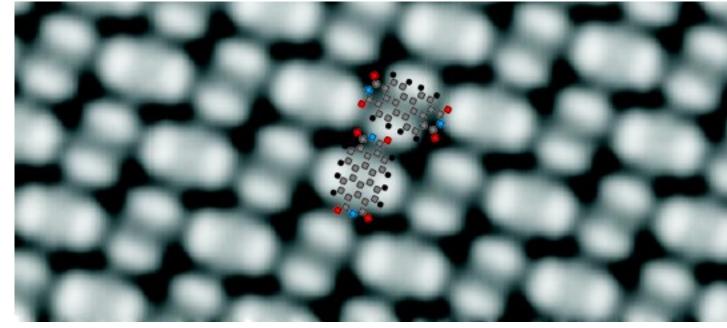
# Modeling switching in STM molecular junctions

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We describe here the investigation of the current switching observed in a molecular junction formed by a PTCDA molecule between an STM tip and an Ag(111) surface, which is believed to be due to the carboxylic oxygen atom switching between the surface and the tip. We use a generalized version of a model developed in 1997 by Gao et al. [1] to investigate the results observed in these experiments. The distribution of the switching events measured in the experiments shows a power law dependence for small bias voltages, whereas for higher voltages it first saturates and then drops again.

### **Experiment**

- Experiments done in the Tautz group at the Forschungszentrum Jülich
- STM measurements on PTCDA on Ag(111)
- Switching between two conductance states for particular tip-surface distances



STM image of PTCDA on Ag(111) [2]

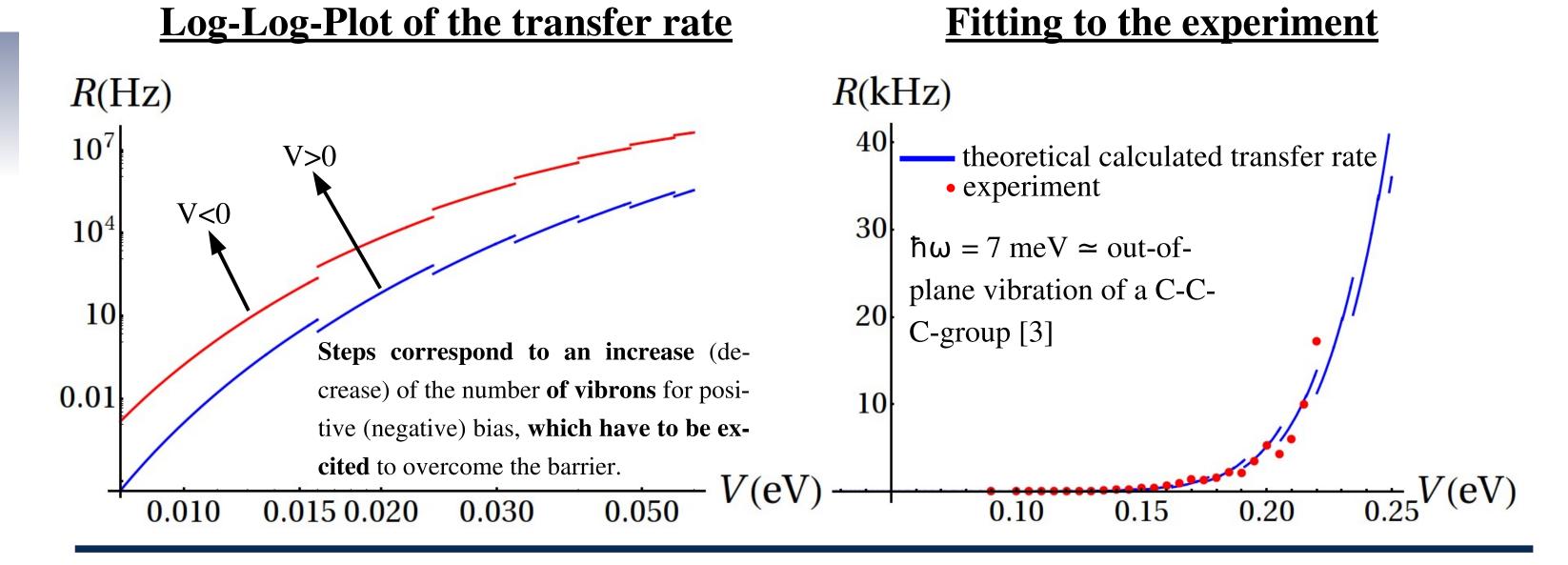
• Switches occur only if the STM-tip is located over the carboxylic oxygen atom (red dots in Fig. 1)

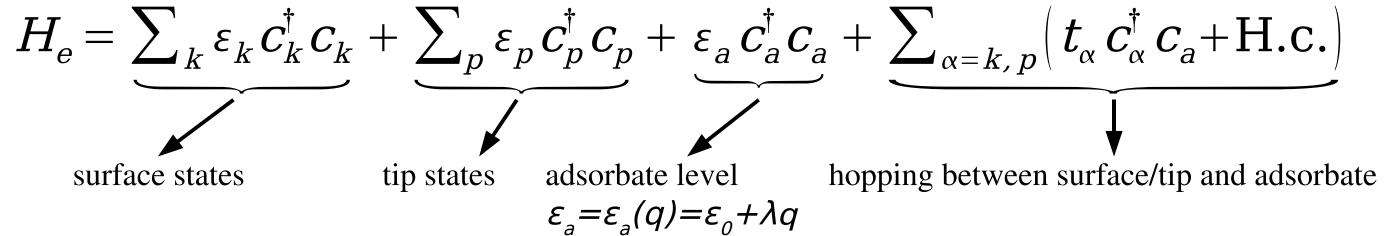
# <u>Model – Transition rates</u>

- System Hamiltonian

# **Results**

- Power law behavior for small bias
- Saturation for higher bias
- For even higher bias the potential changes from a double well to a single well
  - => Transfer rate becomes zero, because molecule stays at the tip or at the surface
- Fitting to measurements is quite demanding, because of many unknown constants
  - => Density Functional Theory (DFT) helps to determine correct values for parameter

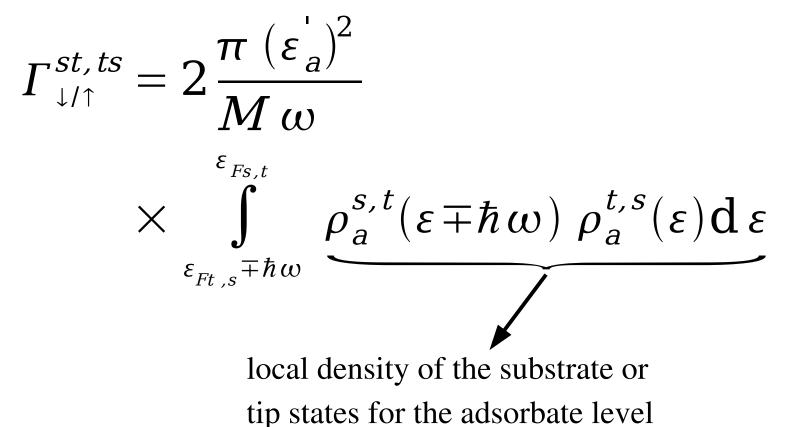


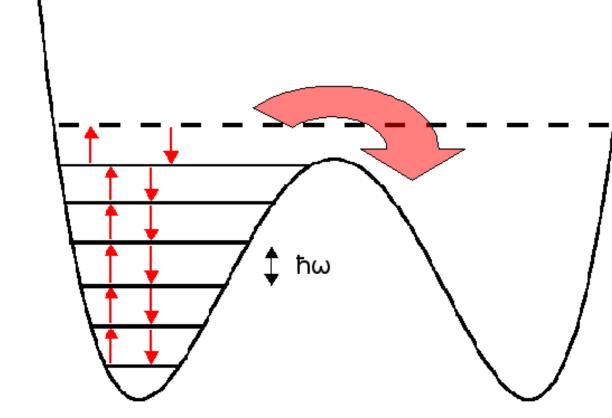


• Electron-vibron interaction  $H_{e-v}$ within first-order perturbation theory => Fermi's golden rule for transition rates

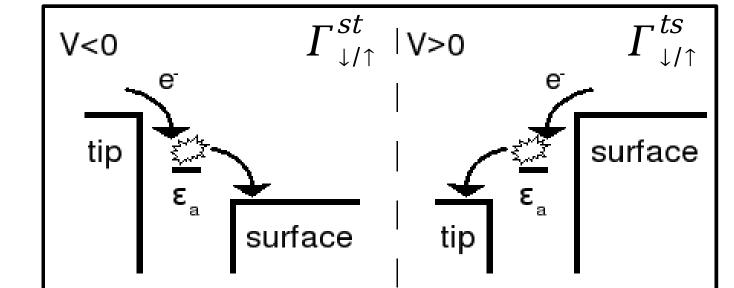
$$\begin{split} \Gamma_{\downarrow\uparrow\uparrow} = 2 \frac{2\pi}{\hbar} \sum_{\nu,\mu} \left| \left\langle \mu, 0/1 \left| H_{\text{e-v}} \right| \nu, 1/0 \right\rangle \right|^2 \\ \times f_{\nu} (1 - f_{\mu}) \, \delta(\varepsilon_{\mu} - \varepsilon_{\nu} \mp \hbar \omega) \end{split}$$

- Low temperatures, adsorbate level within wide-band limit
- Transition rates, e.g.



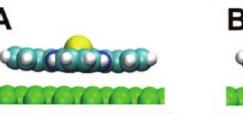


Sketch of our model. The transfer of the PTCDA from surfaces to tip is due to several inelastic scattering events.



#### Other switching mechanism which can be excluded

- Quantum tunneling (probability very small; size of PTCDA)
- Thermal activation (cryogenic STM)



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COCOCO

- Vibrational-assisted, involving 1 vibron (barrier height)
- Switching involving a metastable ionic state (small voltages induce switching)

right: Switching involving a metastable ionic state. SnPc on Ag(111) [4].

# **Conclusion and Outlook**

• Current switching of PTCDA on Ag(111) can be de-

Scattering of electrons tunneling from the STM-tip to the surface via the adsorbate level.

# <u>Model – Transfer rate</u>

- Double well approximated by two truncated harmonic oscillators
- Pauli master equation, only nearest neighbor transitions

$$R = n \Gamma_{\uparrow} \exp\left(-\frac{(n-1)\hbar \omega}{k_b T_v}\right) \simeq n \Gamma_{\uparrow}^n \left(\Gamma_{\downarrow}\right)^{1-n}$$
  
• Linear dependence of barrier  
height (=> n) on the applied bias voltage

scribed by a truncated harmonic oscillator model • Quantitative agreement combining DFT calculations and fitting procedure to determine model parameters

#### • Deeper investigation of the determined parameters

 Introducing temperature and phonon-phonon interaction between surface and adsorbate

### References

[1] S. Gao *et al.*, PRB **55**, 4825 (1997). [2] L. Kilian *et al.*, PRL **100**, 136103 (2008). [3] A.Yu. Kobitski *et al.*, J. Mol. Struc. **625**, 39 (2003). [4] Y. Wang *et al.*, JACS **131**, 3639 (2009).